

Ordering number: EN3752

CMOS LSI

SANYO

LC3517B, BM, BS, BL, BML, BSL
2048-word × 8-bit CMOS Static RAM

OVERVIEW

LC3517B series devices are silicon-gate CMOS, static RAM ICs configured as 2048 words × 8 bits. They incorporate an output enable for high-speed memory access, and TTL-compatible, tristate outputs for direct interfacing with a bus.

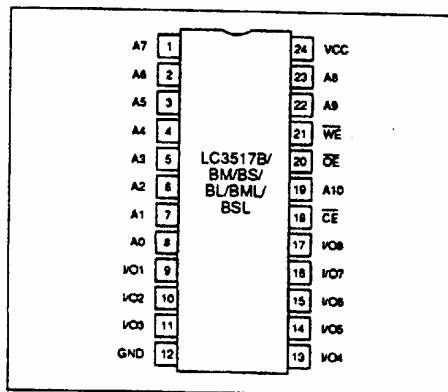
LC3517B series ICs feature a data retention mode and a low standby current, making them ideal for low-power or battery-powered equipment. In particular, the LC3517BL, LC3517BML and LC3517BSL offer a guaranteed maximum standby current of 1 μ A at 60 deg. C.

LC3517B series ICs operate from a 5 V supply and are available in 24-pin DIPs, 24-pin MFPs and 24-pin SDIPs.

FEATURES

- 120 ns (LC3517B-12 series) and 150 ns (LC3517B-15 series) maximum address access times
- 0.2 μ A at 25 deg. C and 1.0 μ A at 60 deg. C (LC3517BL/BML/BSL-12/15), and 5.0 μ A at 60 deg. C and 30 μ A at 85 deg. C (LC3517B/BM/BS-12/15) maximum standby currents
- 9 mA maximum supply current at $f = 1$ MHz
- Data retention for $V_{CC} = 2.0$ to 5.5 V
- Asynchronous operation
- TTL-compatible, tristate input/outputs
- Single 5 V supply
- 24-pin DIP, 24-pin MFP and 24-pin SDIP

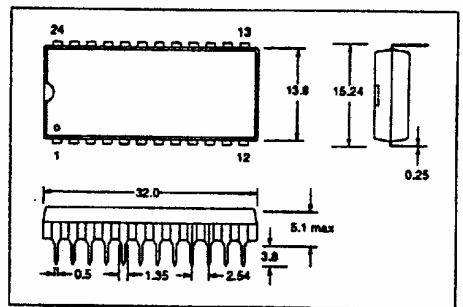
PINOUT



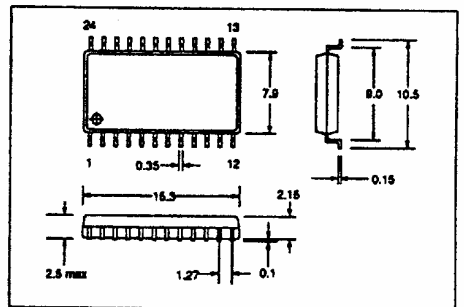
PACKAGE DIMENSIONS

Unit: mm

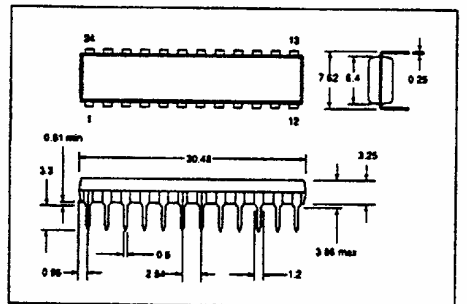
3072-DIP24NS (LC3517B/BL)



3045B-MFP24 (LC3517B/BML)



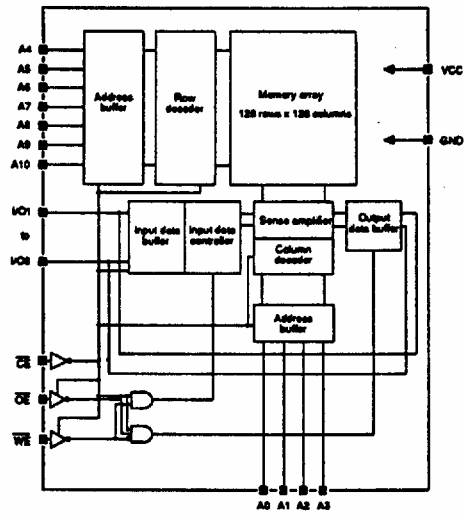
3114-DIP24NS 300 mil (LC3517BS/BSL)



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No. 3752—1/6

BLOCK DIAGRAM



PIN DESCRIPTION

Number	Name	Description
1 to 8, 19, 22, 23	A0 to A10	Address inputs
9 to 11, 13 to 17	I/O1 to I/O8	Data inputs/outputs
12	GND	Ground
18	CE	Chip enable input
20	OE	Output enable input
21	WE	Read/write select input
24	VCC	5 V supply

SPECIFICATIONS

Absolute Maximum Ratings

Parameter	Symbol	Rating	Unit
Supply voltage	V _{CC max}	7.0	V
Input voltage range	V _{ih}	-0.5 to V _{CC} + 0.5	V
Input/output voltage range	V _{io}	-0.5 to V _{CC} + 0.5	V
Operating temperature range	T _{opg}	-30 to 85	deg. C
Storage temperature range	T _{stg}	-55 to 125	deg. C

Recommended Operating Conditions

$T_s = 25 \text{ deg. C}$

Parameter	Symbol	Rating	Unit
Supply voltage	V_{CC}	5.0	V
Supply voltage range	$V_{CC \text{ op}}$	4.5 to 5.5	V

Electrical Characteristics

$V_{CC} = 5 \text{ V} \pm 10\%$, $T_s = -30 \text{ to } 85 \text{ deg. C}$ unless otherwise noted

Parameter	Symbol	Condition	Rating			Unit	
			min	typ	max		
Quiescent supply current	I_{CCQ1}	$V_{EE} = 0 \text{ V}$, $V_{IN} = V_{CC}$ or GND, $I_{VO} = 0 \text{ mA}$	-	2	5	mA	
		$V_{EE} = V_{IL}$, $V_{IN} = V_{IH}$ or V_{OL} , $I_{VO} = 0 \text{ mA}$	-	5	15		
Average supply current	I_{CCQ2}	Minimum cycle time, duty = 100%, $I_{VO} = 0 \text{ mA}$	-	-	50	mA	
		Cycle time = 1 μs , $V_{EE} = 0 \text{ V}$, $V_{IN} = V_{CC}$ or GND, $I_{VO} = 0 \text{ mA}$	-	4	9		
Standby supply current	I_{CCS}	$V_{EE} = V_{CC} - 0.2 \text{ V}$, $V_{IN} = 0 \text{ V}$ to V_{CC} . See note 1.	$T_s = 60 \text{ deg. C}$	-	-	5.0	μA
			$T_s = 85 \text{ deg. C}$	-	-	30	
		$V_{EE} = V_{CC} - 0.2 \text{ V}$, $V_{IN} = 0 \text{ V}$ to V_{CC} . See note 2.	$T_s = 25 \text{ deg. C}$	-	-	0.2	
			$T_s = 60 \text{ deg. C}$	-	-	1.0	
		$V_{EE} = V_{IH}$, $V_{IN} = 0 \text{ V}$ to V_{CC}	-	1.0	3.0	mA	
LOW-level input voltage	V_{IL}		-0.3	-	0.8	V	
HIGH-level input voltage	V_{IH}		2.2	-	$V_{CC} + 0.3$	V	
LOW-level output voltage	V_{OL}	$I_{OL} = 2.0 \text{ mA}$	-	-	0.4	V	
HIGH-level output voltage	V_{OH}	$I_{OH} = -1.0 \text{ mA}$	2.4	-	-	V	
Input capacitance	C_{IN}	$V_{IN} = 0 \text{ V}$, $f = 1 \text{ MHz}$, $T_s = 25 \text{ deg. C}$	-	-	5	pF	
Input/output capacitance	C_{IO}	$V_{VO} = 0 \text{ V}$, $f = 1 \text{ MHz}$, $T_s = 25 \text{ deg. C}$	-	-	10	pF	
Input leakage current	I_{LI}	$V_{IN} = 0$ to V_{CC}	-1.0	-	1.0	μA	
Input/output leakage current	I_{LO}	V_{EE} or $V_{EE} = V_{IH}$, $V_{VO} = 0 \text{ V}$ to V_{CC}	-5.0	-	5.0	μA	

Notes

1. LC3517B/BM/BS-12/15
2. LC3517BL/BML/BSL-12/15
3. Typical values are measured at $V_{CC} = 5.0 \text{ V}$ and $T_s = 25 \text{ deg. C}$.

Timing Characteristics

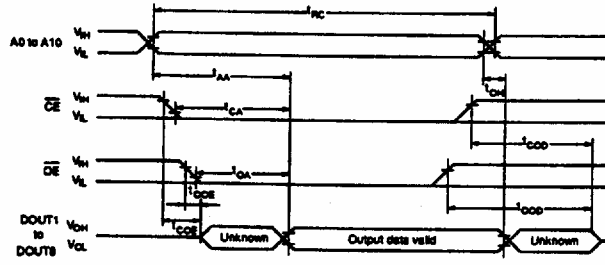
Test conditions

- LOW-level pulse—0.6 V
- HIGH-level pulse—2.4 V
- Input rise and fall times—5 ns
- LOW-level timing reference— $V_{IL} = V_{OL} = 0.8 \text{ V}$

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- HIGH-level timing reference— $V_{IH} = V_{OH} = 2.2\text{ V}$
- Output load—1 TTL gate + $C_L = 100\text{ pF}$ (including jig capacitance)

Read timing

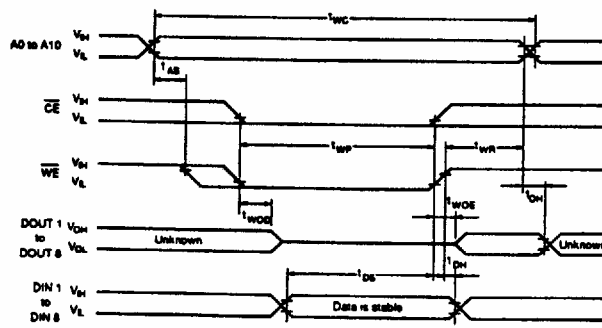


$V_{CC} = 5\text{ V} \pm 10\%$, $T_A = -30\text{ to }85\text{ deg. C}$

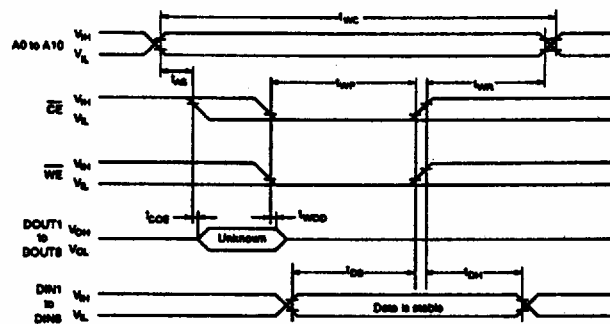
Parameter	Symbol	LC3517B/BM/BS-12, LC3517BL/BML/BSL-12		LC3517B/BM/BS-15, LC3517BL/BML/BSL-15		Unit
		min	max	min	max	
Read cycle time	t_{RC}	120	-	150	-	ns
Address access time	t_{AA}	-	120	-	150	ns
Output-enable access time	t_{OA}	-	70	-	80	ns
Chip-enable access time	t_{CA}	-	120	-	150	ns
Output hold time	t_{OH}	20	-	20	-	ns
Output-enable propagation delay	t_{OOE}	5	-	5	-	ns
Chip-enable propagation delay	t_{OCE}	10	-	10	-	ns
Output-disable propagation delay	t_{OOD}	-	40	-	50	ns
Chip-disable propagation delay	t_{COD}	-	40	-	50	ns

Write timing

Write cycle 1



Write cycle 2



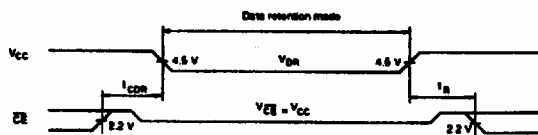
V_{CC} = 5 V ±10%, T_a = -30 to 85 deg. C

Parameter	Symbol	LC3517B/BM/BS-12, LC3517BL/BML/BSL-12		LC3517B/BM/BS-15, LC3517BL/BML/BSL-15		Unit
		min	max	min	max	
Write cycle time	t _{wc}	120	-	150	-	ns
Address setup time	t _{as}	0	-	0	-	ns
Write pulsewidth	t _{wp}	100	-	120	-	ns
Write recovery time	t _{wr}	0	-	0	-	ns
Data setup time	t _{ds}	60	-	70	-	ns
Data hold time	t _{dh}	0	-	0	-	ns
Write-enable propagation delay	t _{wce}	5	-	5	-	ns
Write-disable propagation delay	t _{wod}	-	40	-	50	ns

Notes

1. Hold WE HIGH during the read cycle.
2. Do not apply opposite phase signals to DOUT when it is connected to the output bus.
3. t_{wr} is measured when CE and WE are LOW.
4. t_{wa}, t_{de} and t_{dh} are measured when CE or WE is HIGH.
5. DOUT becomes high impedance when either CE or OE is HIGH, or WE is LOW.
6. t_{as} is measured when CE and WE are LOW.
7. DOUT is high impedance when OE is HIGH during the write cycle.
8. DOUT has the same phase as the data to be written during the write cycle.
9. DOUT is the data read out from the next address.

Data Retention Characteristics



LC3517B, BM, BS, BL, BML, BSL

T_a = -30 to 85 deg. C

Parameter	Symbol	Condition	Rating			Unit	
			min	typ	max		
Data retention mode supply voltage	V _{DR}	V _{CE} = V _{CC} , V _{IN} = 0 V to V _{CC}	2.0	-	5.5	V	
Data retention mode supply current	I _{CCDR}	V _{CE} = V _{CC} , V _{CC} = 3.0 V, V _{IN} = 0 V to V _{CC} . See note 1.	T _a = 60 deg. C	-	-	4.0	μA
			T _a = 85 deg. C	-	-	20	
		V _{CE} = V _{CC} , V _{CC} = 3.0 V, V _{IN} = 0 V to V _{CC} . See note 2.	T _a = 25 deg. C	-	-	0.2	
			T _a = 60 deg. C	-	-	1.0	
Chip-enable setup time	t _{CON}		0	-	-	ns	
Chip-enable hold time	t _H		t _{HC}	-	-	ns	

Notes

1. LC3517B/BM/BS-12/15
2. LC3517BL/BML/BSL-12/15

Mode Selection

Mode	\overline{CE}	\overline{DE}	\overline{WE}	I/O1 to I/O8	Supply current
Read	L	L	H	Data input	I _{CCA}
Write	L	X	L	Data output	I _{CCA}
Output disable	L	H	X	High impedance	I _{CCA}
Standby	H	X	X	High impedance	I _{CCS}

Note
X = don't care

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